

# TIS97\_D26Z Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number TIS97\_D26Z-DG

Manufacturer onsemi

Manufacturer Product Number TIS97\_D26Z

Description TRANS NPN 40V 0.5A TO92-3

Detailed Description Bipolar (BJT) Transistor NPN 40 V 500 mA 625 mW T

hrough Hole TO-92-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



TIS97

# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
TIS97_D26Z	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
40 V	
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10nA (ICBO)	250 @ 100μA, 5V
Power - Max:	Frequency - Transition:
625 mW	
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA) Formed Leads	TO-92-3
Base Product Number:	

# **Environmental & Export classification**

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.21.0095



#### Discrete POWER & Signal **Technologies**

## **TIS97**



# **NPN General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100 for characteristics.

#### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	40	V	
V <sub>CBO</sub>	Collector-Base Voltage	40	V	
$V_{EBO}$	Emitter-Base Voltage	6.0	V	
I <sub>C</sub>	Collector Current - Continuous	500	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range -55 to +150 °C		°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics**

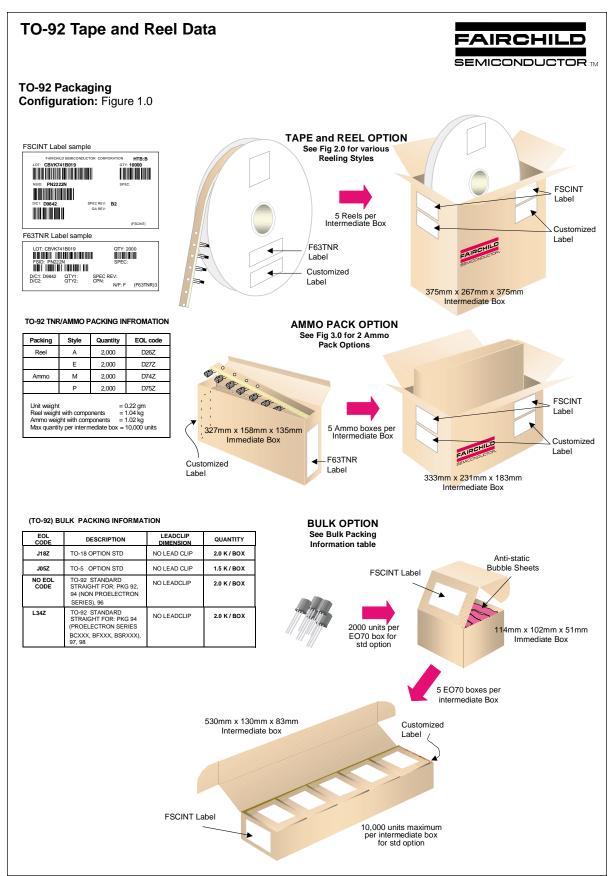
TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TIS97	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# NPN General Purpose Amplifier (continued)

Electr	Electrical Characteristics TA = 25°C unless otherwise noted				
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	40		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 40 \text{ V}, I_{E} = 0$ $V_{CB} = 60 \text{ V}, I_{E} = 0$		10 10	nA μA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 6.0 \text{ V}, I_{C} = 0$		20	nA
ON CHAR	ACTERISTICS*  DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	250	700	
					V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	0.45	0.65	V
SMALL S	IGNAL CHARACTERISTICS				
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	1.0	4.0	pF
C <sub>eb</sub>	Emitter-Base Capacitance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$		16	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_C = 100 \mu A, V_{CE} = 5.0 V,$ f = 1.0 kHz $I_C = 10 mA, V_{CE} = 5.0 V,$	250	800	
NF	Noise Figure	f = 100 MHz	2.0		
INF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_{C} = 30 \mu\text{A},$ $R_{g} = 10 \text{ k}\Omega, f = 1.0 \text{ kHz},$ $B_{W} = 100 \text{ Hz}$		2.0	dB
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A},$ $R_{g} = 10 \text{k}\Omega, \; B_{W} = 15.7 \text{kHz}$		3.0	dB

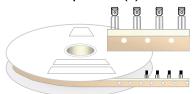
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%



### TO-92 Tape and Reel Data, continued

#### **TO-92 Reeling Style** Configuration: Figure 2.0

#### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

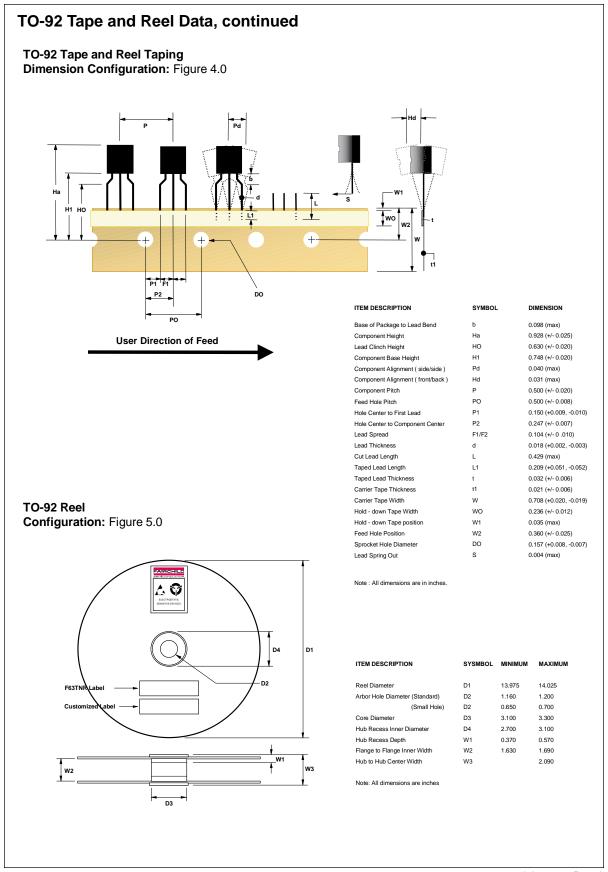
Style "E", D27Z, D71Z (s/h)

#### **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0





FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP



# **TO-92 Package Dimensions** FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 92 94 96 В В B F В D 2 В S С G Ε D Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

 $ACEx^{TM}$ FASTr™ PowerTrench® SyncFET™ Bottomless™ QFET™ TinyLogic™ GlobalOptoisolator™ QSTM UHC™ CoolFET™ GTO™  $VCX^{TM}$  $CROSSVOLT^{TM}$ QT Optoelectronics™ HiSeC™

EnSigna<sup>TM</sup> OPTOLOGIC<sup>TM</sup> SMART START<sup>TM</sup>
FACT<sup>TM</sup> OPTOPLANAR<sup>TM</sup> SuperSOT<sup>TM</sup>-3
FACT Quiet Series<sup>TM</sup> PACMAN<sup>TM</sup> SuperSOT<sup>TM</sup>-6
FAST ® POP<sup>TM</sup> SuperSOT<sup>TM</sup>-8

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



## **OUR CERTIFICATE**

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

















Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com